

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- DC Motor Control
- Welding
- Battery Chargers

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V_{DRM} V_{RRM} V	Conditions
DCR818SG48	4800	$T_{vj} = 0^\circ$ to 125°C , $I_{DRM} = I_{RRM} = 75\text{mA}$, $V_{DRM}, V_{RRM}, t_p = 10\text{ms}$, $V_{DSM} \& V_{RSM} =$ $V_{DRM} \& V_{RRM} + 100\text{V}$ Respectively
DCR818SG47	4700	
DCR818SG46	4600	
DCR818SG45	4500	
DCR818SG44	4400	

Lower voltage grades available.

KEY PARAMETERS

V_{DRM}	4800V
$I_{T(AV)}$	529A
I_{TSM}	7500A
dV/dt^*	1000V/μs
dI/dt	150A/μs

*Higher dV/dt selections available

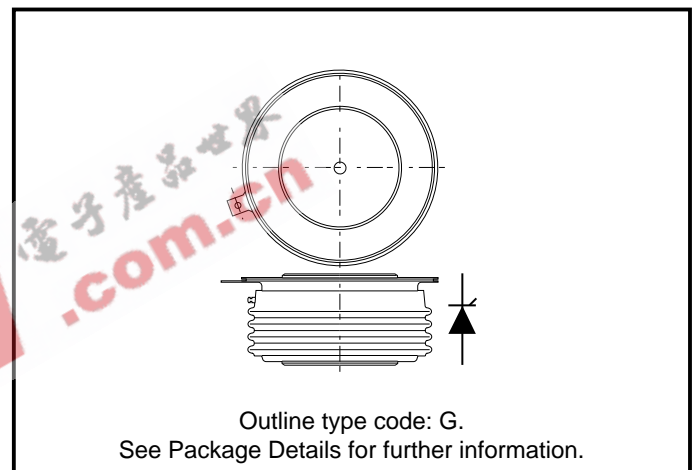


Fig.1 Package outline

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR818SG46

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

CURRENT RATINGS

 $T_{\text{case}} = 60^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	529	A
$I_{T(RMS)}$	RMS value	-	830	A
I_T	Continuous (direct) on-state current	-	756	A
Single Side Cooled (Anode side)				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	349	A
$I_{T(RMS)}$	RMS value	-	548	A
I_T	Continuous (direct) on-state current	-	464	A

CURRENT RATINGS

 $T_{\text{case}} = 80^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	425	A
$I_{T(RMS)}$	RMS value	-	667	A
I_T	Continuous (direct) on-state current	-	595	A
Single Side Cooled (Anode side)				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	285	A
$I_{T(RMS)}$	RMS value	-	447	A
I_T	Continuous (direct) on-state current	-	360	A

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine; $T_{case} = 125^{\circ}C$	6.0	kA
I^2t	I^2t for fusing	$V_R = 50\% V_{RRM}$ - 1/4 sine	0.18×10^6	A ² s
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine; $T_{case} = 125^{\circ}C$	7.5	kA
I^2t	I^2t for fusing	$V_R = 0$	0.28×10^6	A ² s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions	Min.	Max.	Units	
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.032	$^{\circ}C/W$
		Single side cooled	Anode dc	-	0.064	$^{\circ}C/W$
			Cathode dc	-	0.064	$^{\circ}C/W$
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Clamping force 12kN with mounting compound	Double side	-	0.008	$^{\circ}C/W$
			Single side	-	0.016	$^{\circ}C/W$
T_{vj}	Virtual junction temperature	On-state (conducting)	-	135	$^{\circ}C$	
		Reverse (blocking)	-	125	$^{\circ}C$	
T_{stg}	Storage temperature range		-55	125	$^{\circ}C$	
-	Clamping force		10.8	13.2	kN	

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Conditions	Typ.	Max.	Units	
I_{RRM}/I_{DRM}	Peak reverse and off-state current	At V_{RRM}/V_{DRM} , $T_{case} = 125^{\circ}C$	-	50	mA	
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125^{\circ}C$.	-	1000	V/ μ s	
dI/dt	Rate of rise of on-state current	From 67% V_{DRM} to 1000A Gate source 20V, 10 Ω $t_r \leq 0.5\mu$ s. $T_j = 125^{\circ}C$.	Repetitive 50Hz	-	75	A/ μ s
			Non-repetitive	-	150	A/ μ s
$V_{T(To)}$	Threshold voltage	At $T_{vj} = 125^{\circ}C$	-	1.4	V	
r_T	On-state slope resistance	At $T_{vj} = 125^{\circ}C$	-	1.7	m Ω	
t_{gd}	Delay time	$V_D = 67\% V_{DRM}$, Gate source 30V, 15 Ω Rise time 0.5 μ s, $T_j = 25^{\circ}C$	-	1.7	μ s	
I_L	Latching current	$T_j = 25^{\circ}C$, $V_D = 5V$, Gate source = 20V, 10 Ω	100	1000	mA	
I_H	Holding current	$T_j = 25^{\circ}C$, $R_{g-k} = \infty$	60	500	mA	
t_q	Turn-off time	$I_T = 1000A$, $t_p = 1ms$, $T_j = 125^{\circ}C$, $V_{RM} = 100V$, $dI_{RR}/dt = 10A/\mu$ s, $dV_{DR}/dt = 20V/\mu$ s to 3000V	450	-	μ s	

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	3.0	V
I_{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	300	mA
V_{GD}	Gate non-trigger voltage	At V_{DRM} , $T_{case} = 125^{\circ}C$	0.25	V
V_{FGM}	Peak forward gate voltage	Anode positive with respect to cathode	30	V
V_{FGN}	Peak forward gate voltage	Anode negative with respect to cathode	0.25	V
V_{RGM}	Peak reverse gate voltage		5	V
I_{FGM}	Peak forward gate current	Anode positive with respect to cathode	10	A
P_{GM}	Peak gate power	See table, fig.5	150	W
$P_{G(AV)}$	Mean gate power		5	W

CURVES

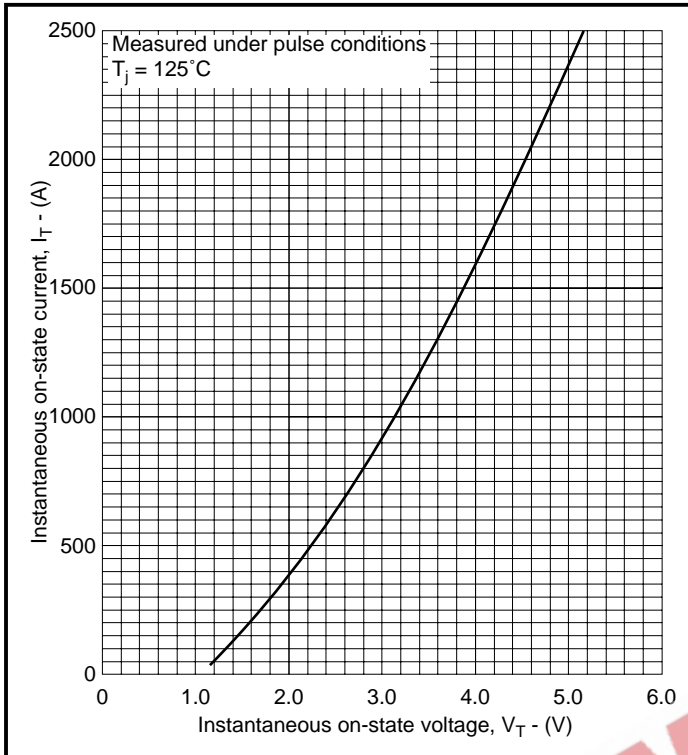


Fig.2 Maximum (limit) on-state characteristics

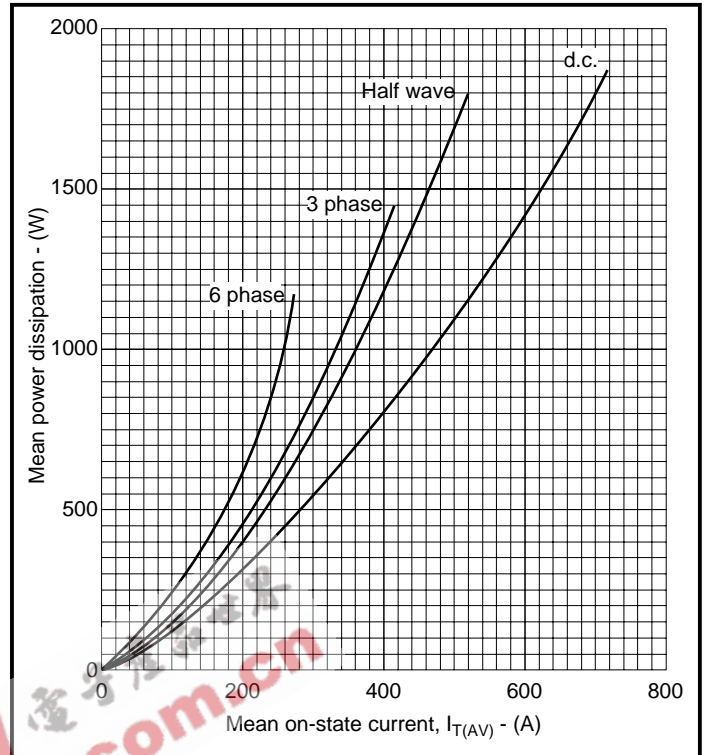


Fig.3 Dissipation curves

V_{TM} Equation:-

$$V_{TM} = A + B \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

Where

- A = 0.650046
- B = -0.018621
- C = 0.000589
- D = 0.063601

these values are valid for $T_j = 125^\circ\text{C}$ for I_T 500A to 2500A

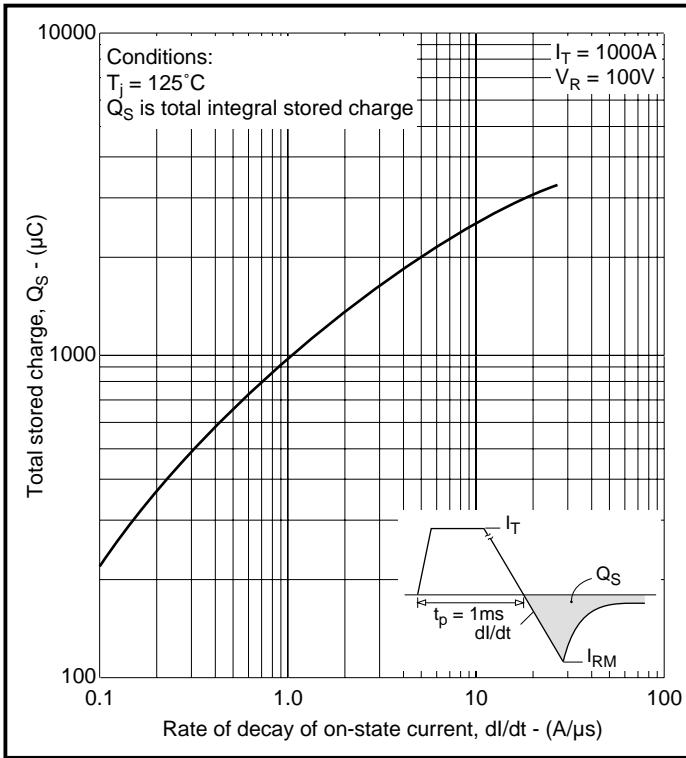


Fig.4 Stored charge

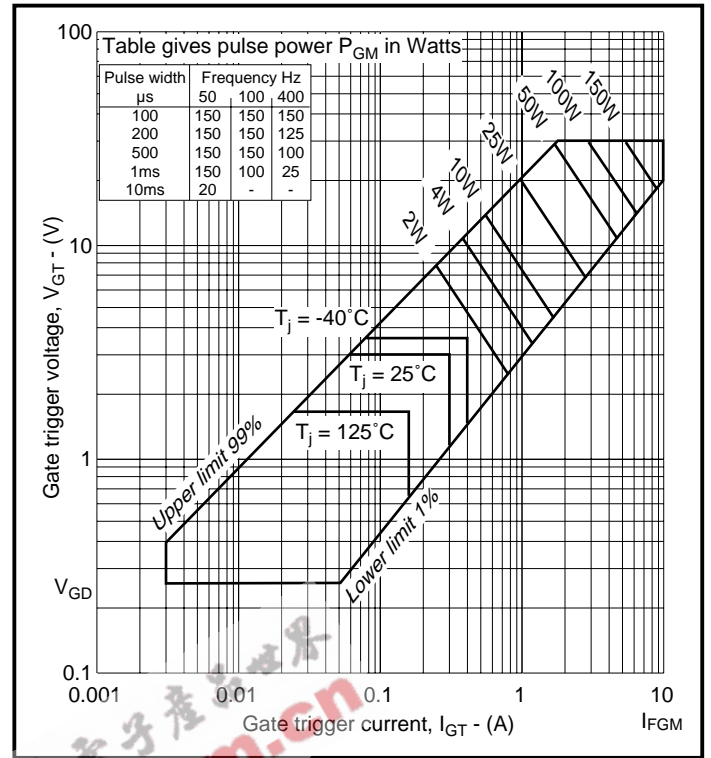


Fig.5 Gate characteristics

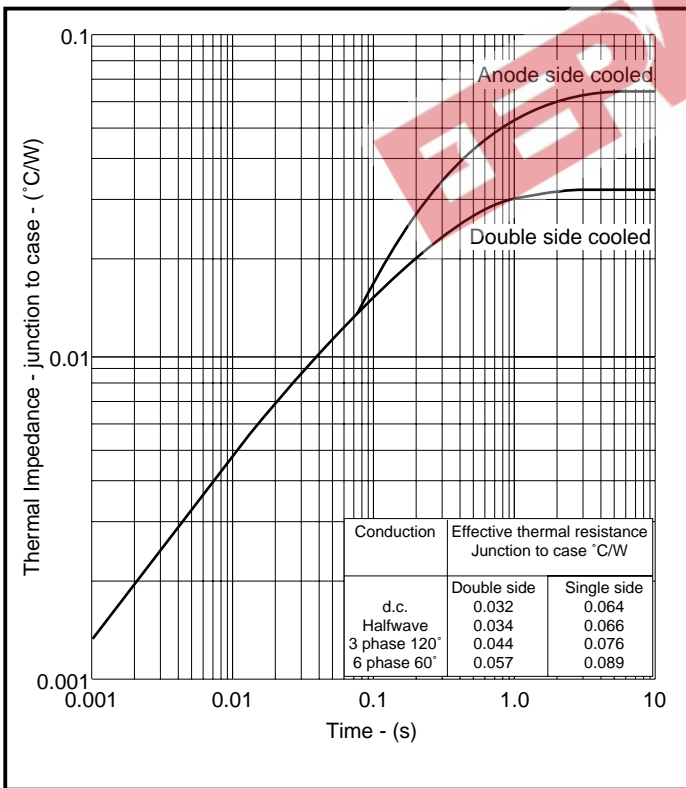


Fig.6 Transient thermal impedance - junction to case

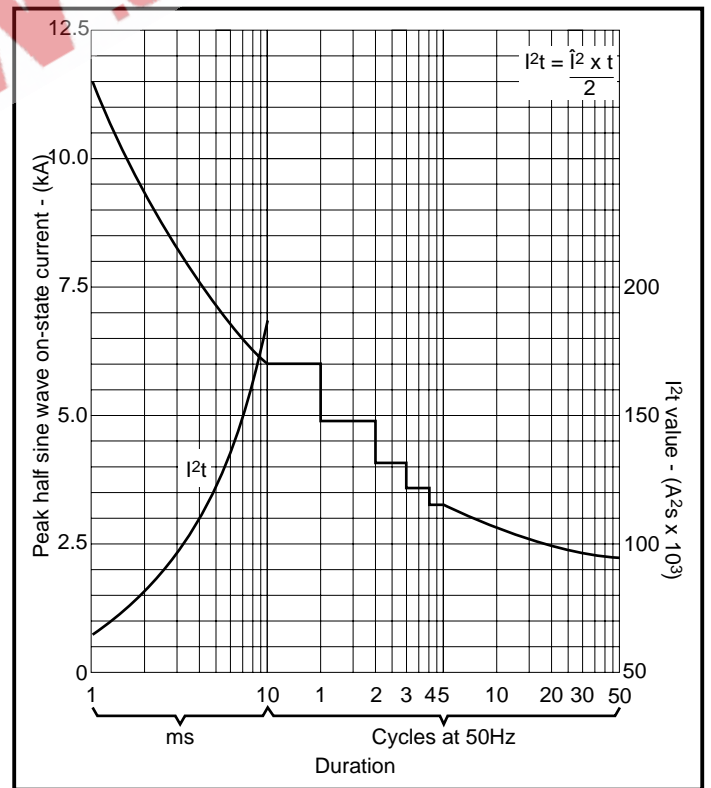
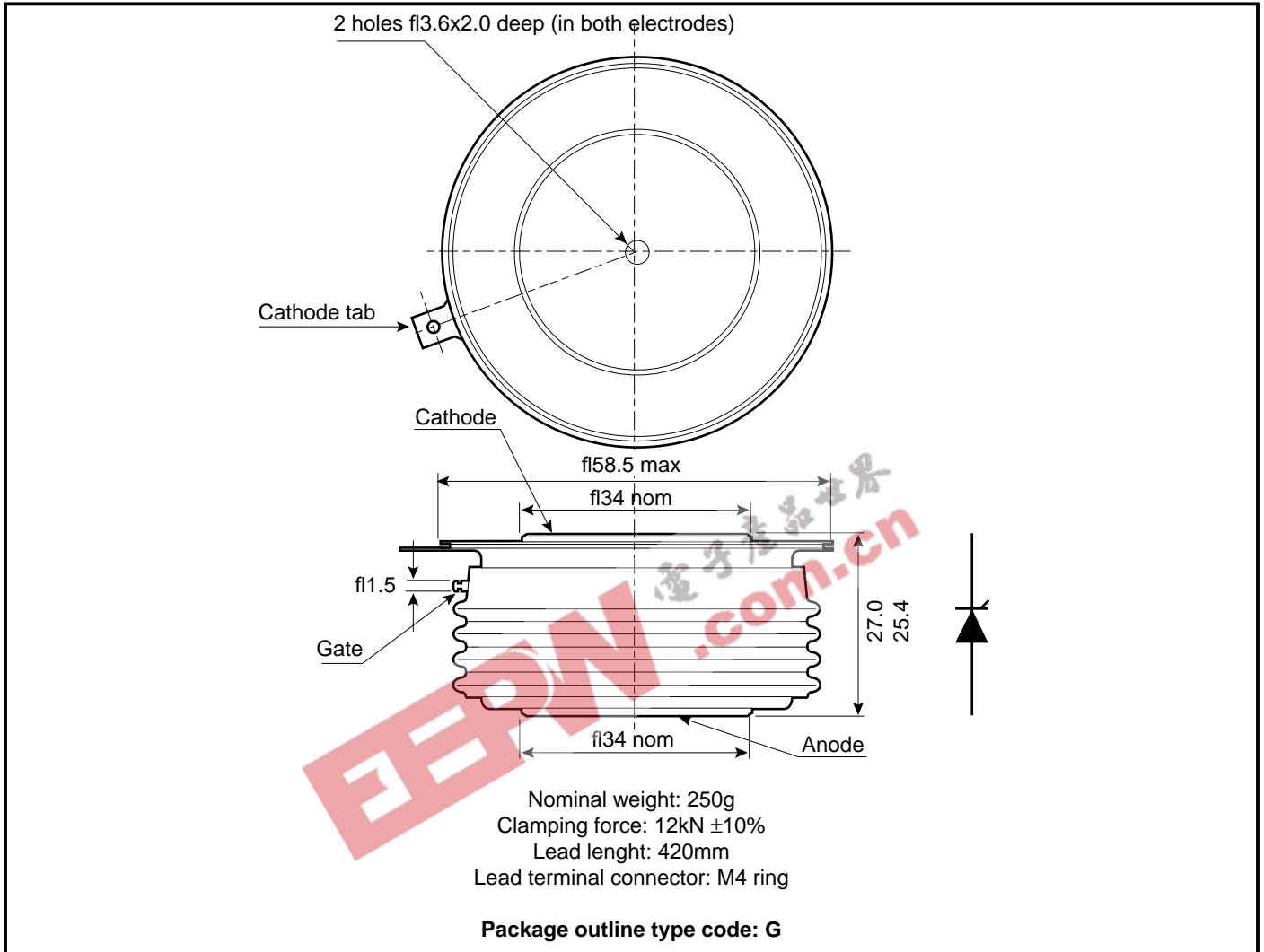


Fig.7 Surge (non-repetitive) on-state current vs time (with 50% V_{RRM} at $T_{case} = 125^\circ C$)

PACKAGE DETAILS

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink / clamping systems in line with advances in device types and the voltage and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group continues to offer high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the up to date CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete solution (PACs).

DEVICE CLAMPS

Disc devices require the correct clamping force to ensure their safe operation. The PACs range offers a varied selection of pre-loaded clamps to suit all of our manufactured devices. This include cube clamps for single side cooling of 'T' 22mm

Clamps are available for single or double side cooling, with high insulation versions for high voltage assemblies.

Please refer to our application note on device clamping, AN4839

HEATSINKS

Power Assembly has its own proprietary range of extruded aluminium heatsinks. They have been designed to optimise the performance of our semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest Sales Representative or Customer Services.



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Preliminary Information: The product is in design and development. The datasheet represents the product as it is understood but details may change.

Advance Information: The product design is complete and final characterisation for volume production is well in hand.

No Annotation: The product parameters are fixed and the product is available to datasheet specification.

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